

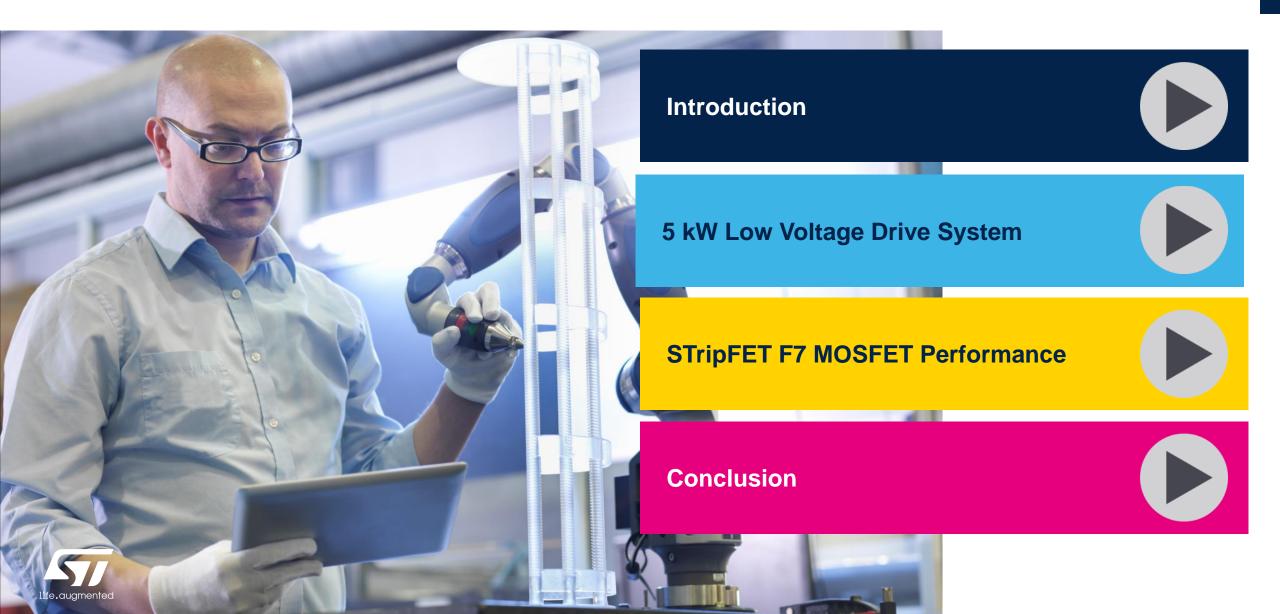


Safe and efficient control and drive solution for 48V industrial motors

STMicroelectronics

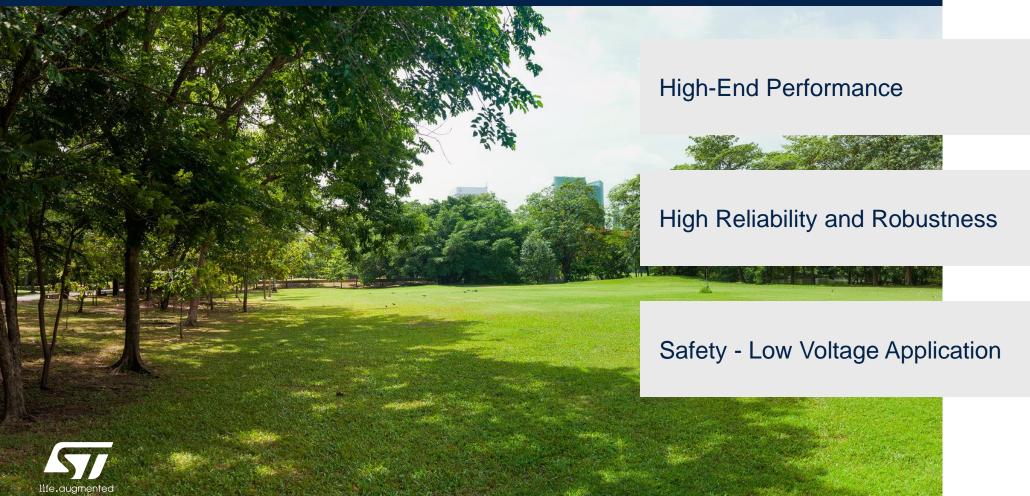


48V drive system: more efficiency and safety



Introduction

Battery Operated Low Voltage Drive System







Low voltage drive system overview

- Battery Operated LV Drive System
 - Higher Reliability
 - Improved Performance/Cost Ratio
 - Reduced Risk of Electric Injury
- Target Applications:
 - Forklifts and Golf Carts
 - Low Speed EV and E-Bikes
 - Professional Power and Garden Tools
 - Robots and Vacuum Cleaners









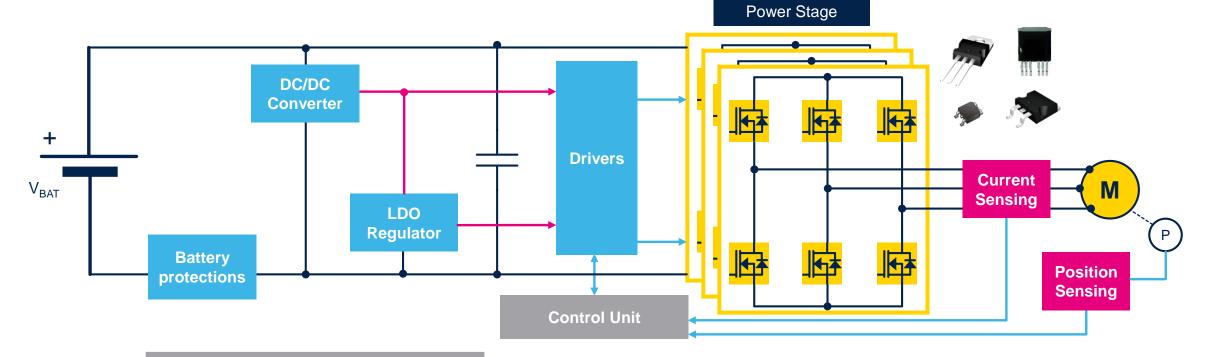




Typical drive system structure

Driver stage: High performance gate drivers, Smart shutdown, Interlocking

Power Stage: Reliability, Robustness



Control Stage: Driving algorithm, Safety procedures









Drive system – key products

- STMicroelectronics is able to cover all the functional segments
- Power Stage Power MOSFETs STripFET F7 Technology
 - Enhanced trench gate structure offering a very low on-resistance
 - Optimized C_{rss}/C_{iss} ratio to reduce EMI emissions
- Driver Stage High Performance Gate Drivers
 - High current capability and high switching performance
 - Smart protections Smart shutdown, interlocking, comparators
- Control Stage 32 bit Arm® core MCU
 - Computational power to execute FOC algorithm















40 ÷ 100 V STripFET F7 family

40 ÷ 100 V STripFET F7 Family optimized for LV Motor Control

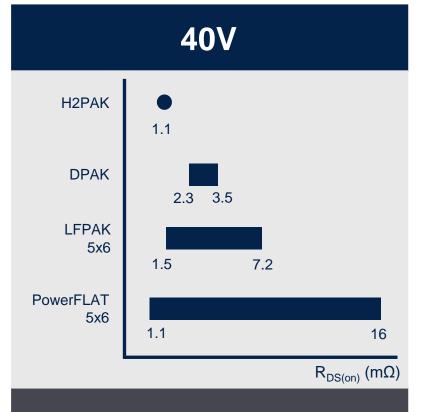


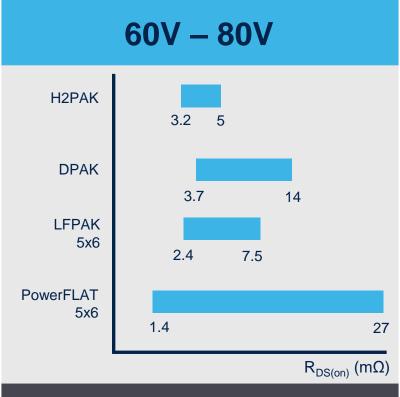


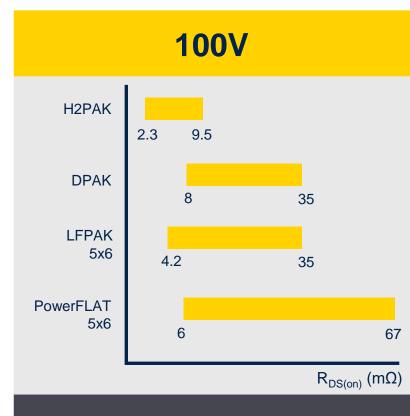




F7 product portfolio: +100 products







ST MOSFET Finder















5 kW low voltage drive system

5 kW Low Voltage Drive System Based on STripFET F7 Family







5 kW low voltage drive system - overview

- Stackable solution
 - Power stage
 - Bulk capacitor board
 - Gate driver board
 - Current sensing board
- Motor Control Connector
 - Enables easy interfacing between control and power board
 - Fully compatible with ST Motor Control FOC library
 - Sensored and sensorless operation
- IMS for better heat exchange
- Protections OC, UV, OV and thermal protection





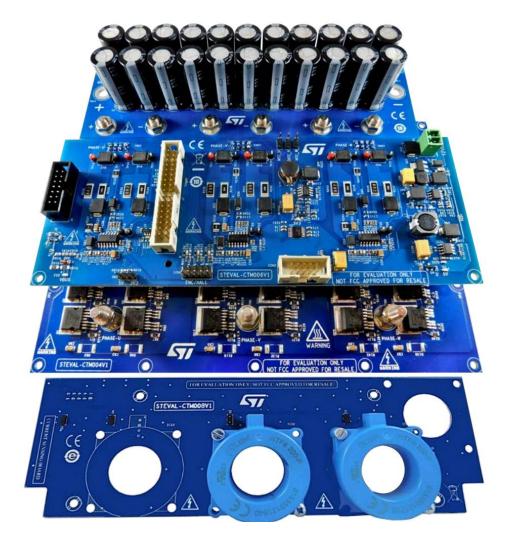






5 kW LV drive STEVAL-CTM009V1

- <u>STEVAL-CTM009V1</u> Key Components:
 - STH310N10F7-6: 100 V F7 MOSFET 6 in parallel
 - L6491: High Side and Low Side driver
 - A7986: Buck Boost switching regulator up to 3A
 - A6902: Buck switching regulator up to 1A
 - Also available in AG <u>STEVAL-TTM001V1</u>





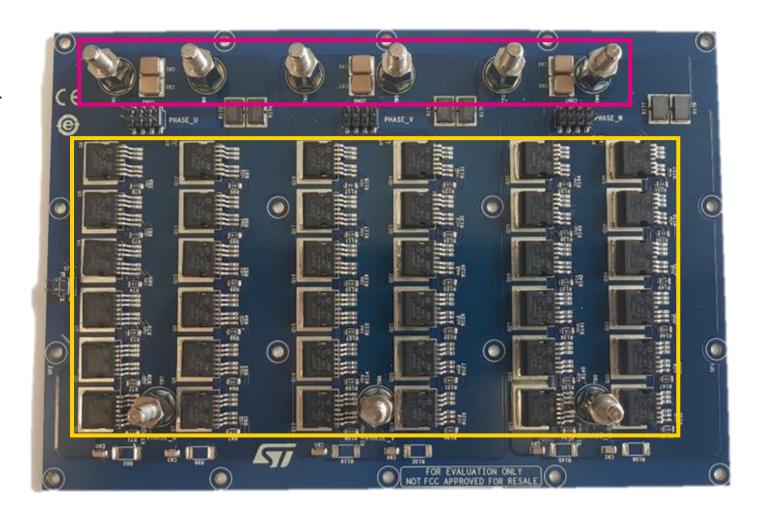




5 kW LV drive system – power board

Key Features:

- Insulated Metal Substrate (IMS) for a better heat distribution
- 36x **STripFET MOSFETs** in **H2PAK-6**
- 3 symmetrical power path for optimized switching (ringing reduced)
- 3 Independent DC Bus connections (one on each leg)
- Decoupling gate resistors (2.2 Ohm) on each gate MOSFET
- 3 Shunt resistors ground referred (500 μOhm) for OC/SC protection
- 3 NTCs for temperature monitoring and thermal protection
- Snubber circuitry on each switch











5 kW LV drive system – driver board

• L6491 half-bridge driver:

- Current capability up to 4 A sink/source
- Independent driving paths with optimized R_{gon} and R_{goff}
- Integrated bootstrap diodes
- Comparators for fault detection
- Interlocking feature
- Adjustable deadtime

Driver Section



Current Sensing Connector





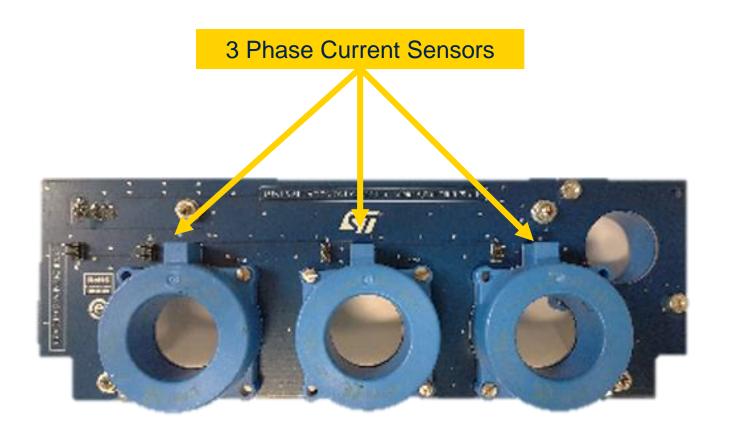




5 kW LV drive system – current sensing board

Key Features:

- Galvanic separation for improved signal to noise ratio (insulation not required for safety)
- High immunity to external interference
- Accuracy <1% at 200A
- Non linearity error < 0.5%









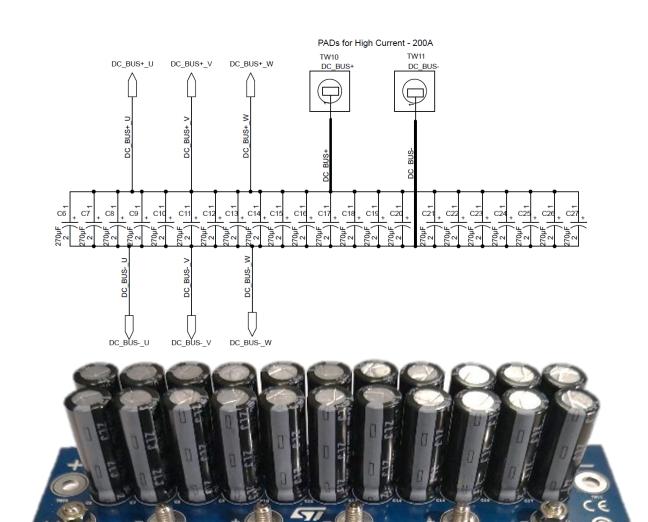


5 kW LV drive system – bulk capacitor board

- Bus Link Capacitors:
 - Reduce current ripple

Suppress voltage spikes

 Designed to withstand current ripple caused by low inductance motors



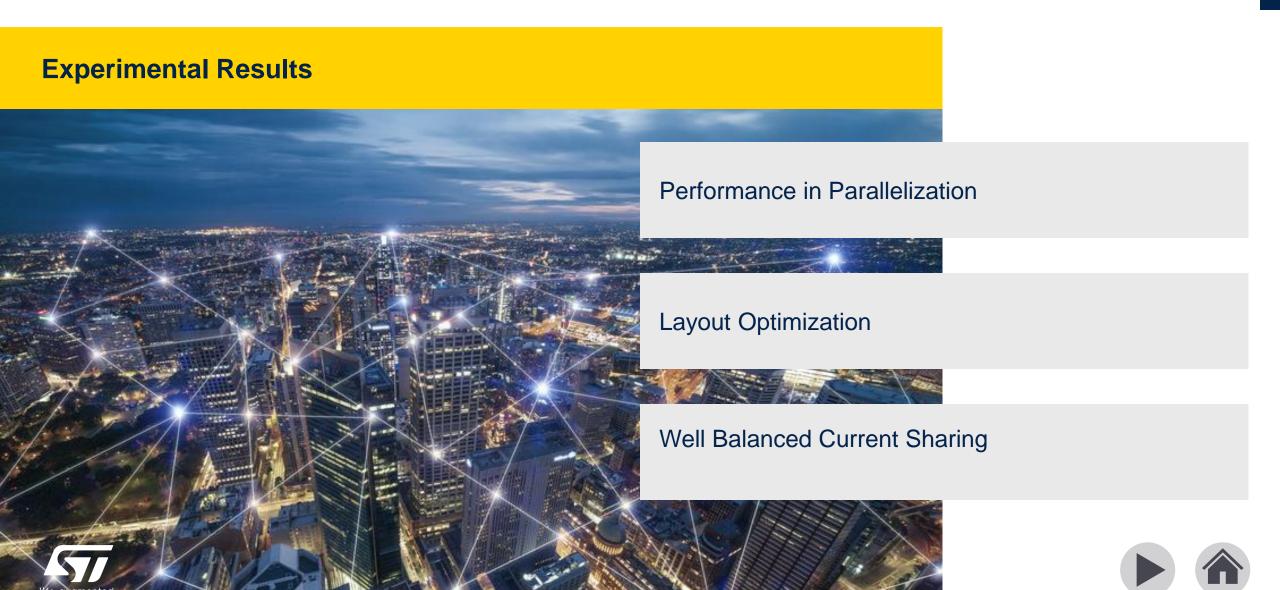






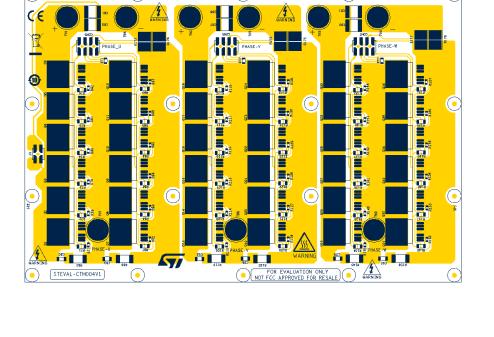


STripFET F7 MOSFETs performance



Design: layout optimization

- Requirements for proper parallelization:
 - Similar V_{gsth} (IC selection)
 - IC well displaced (thermally coupled)
 - Low parasitic inductance
 - Symmetrical path (power and driving path)
 - Asymmetric driving (different R_{gon} and R_{goff})



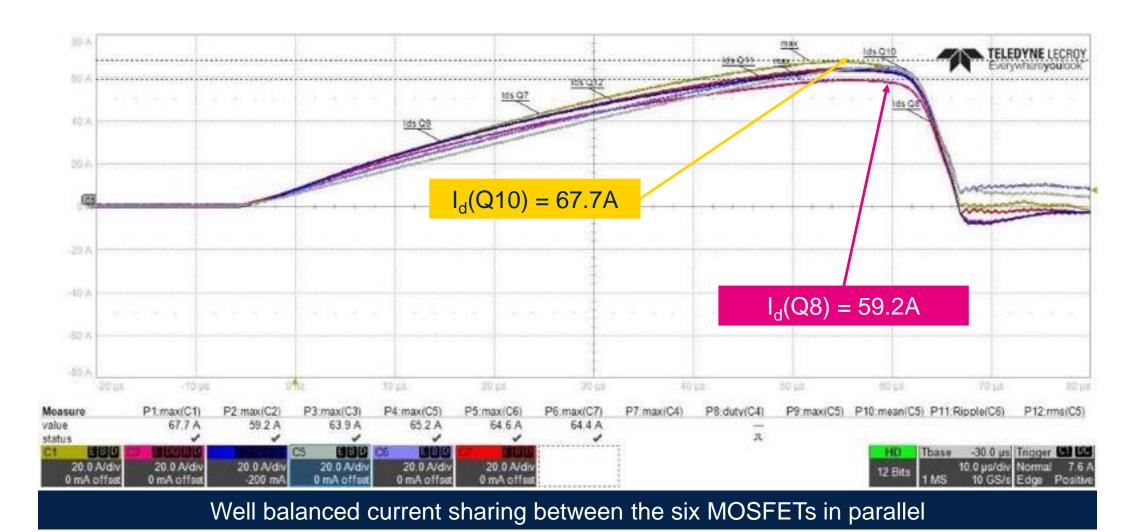








Current sharing in MOSFETs



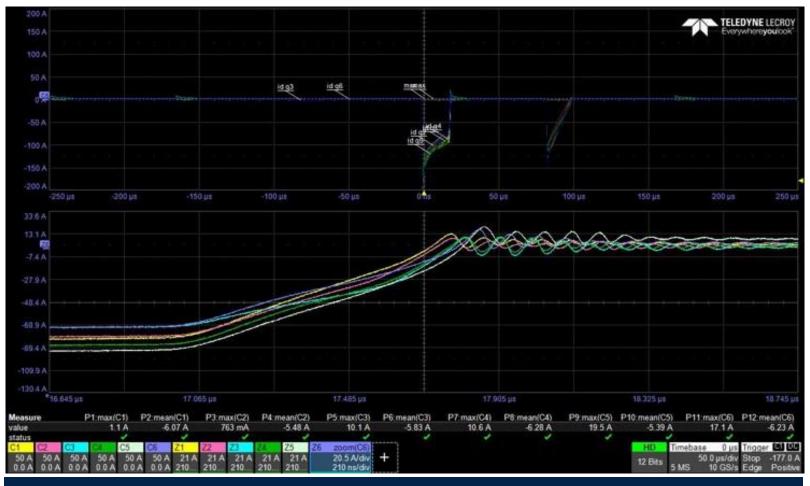








Current sharing in body diodes



Reverse recovery body drain currents are well balanced among the six MOSFETs in parallel







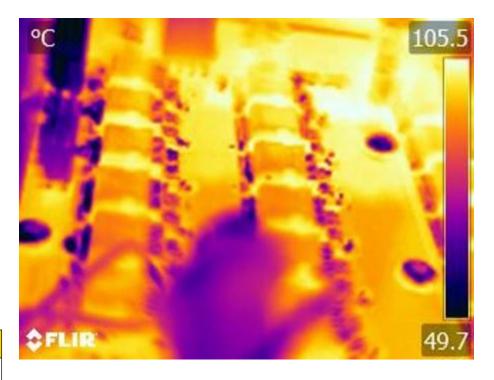


Thermal performance

- Test at 4.5 kW Output Power
- Picture after 40 minutes of operation
- Temperature safely below 175°C
- At the 90% of max load the max temperature is below 105°C.

| | Device: STH310N10F7 | | | | | | | | | | | |
|-----------------------------|--------------------------------------|------|-------|-------|-------|-------|-------------------------------------|--------|-------|-------|-------|-------|
| | High Side U _{phase} MOSFETs | | | | | | Low Side U _{phase} MOSFETs | | | | | |
| Case Temperature [°C] | Q1 | Q2 | Q3 | Q4 | Q5 | Q6 | Q7 | Q8 | Q9 | Q10 | Q11 | Q12 |
| max. | 99.5 | 99.8 | 100.4 | 101.2 | 102.4 | 101.5 | 98.5 | 101.9 | 103.4 | 104.5 | 104.3 | 104.9 |
| min. | 85.9 | 81.1 | 91.9 | 91.9 | 87.9 | 93.3 | NA (*) | NA (*) | 88.6 | 90.1 | 94.9 | 103.5 |
| average | 94.6 | 91.6 | 98.8 | 96.2 | 96.7 | 97.4 | NA (*) | NA (*) | 94.5 | 96.7 | 99.9 | 101.9 |

(*) due to an obstacle along the measurement line





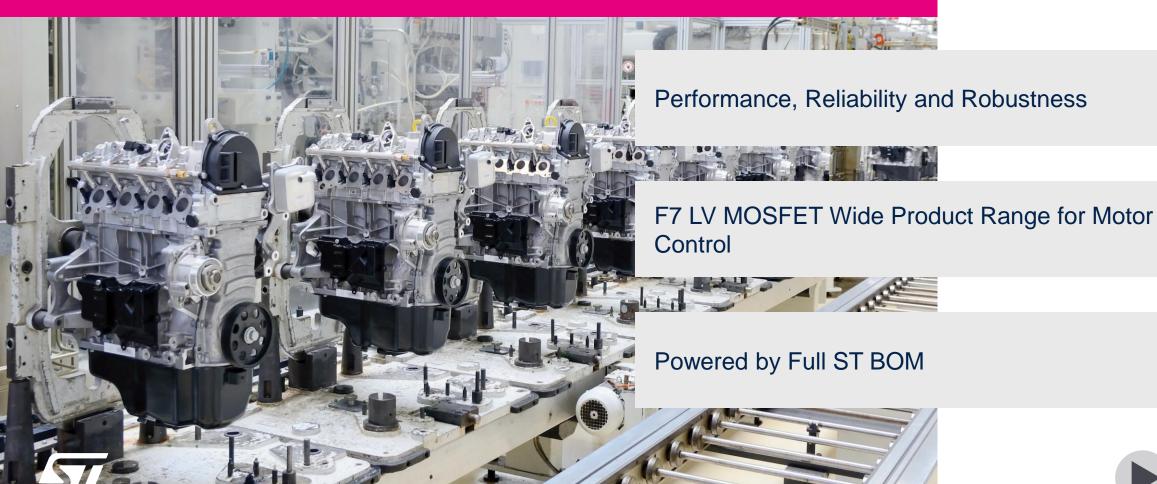






Conclusion









Thank you



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